

## SOT-23 Plastic-Encapsulate Transistors

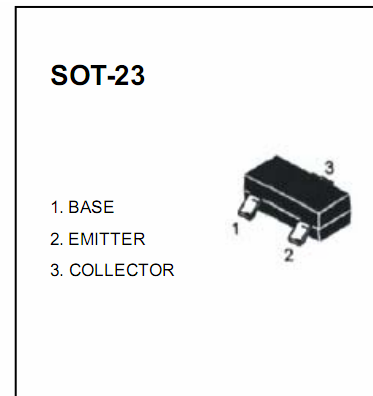
**S9015** TRANSISTOR (PNP)

**FEATURES**

Complimentary to S9014

MARKING:M6

**MAXIMUM RATINGS** (TA=25°C unless otherwise noted)



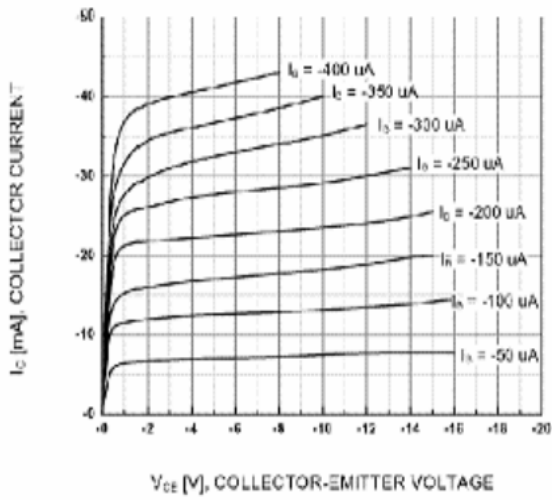
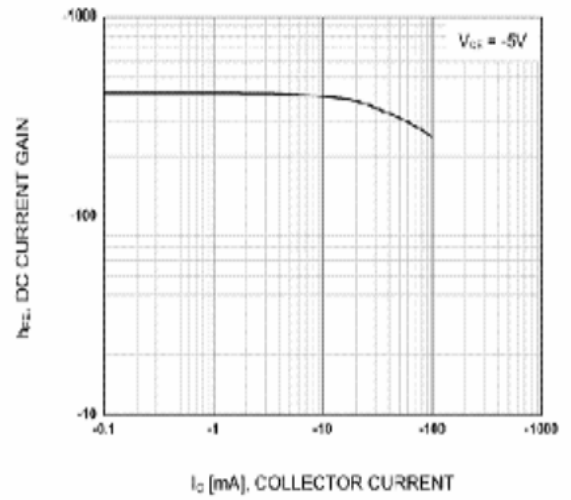
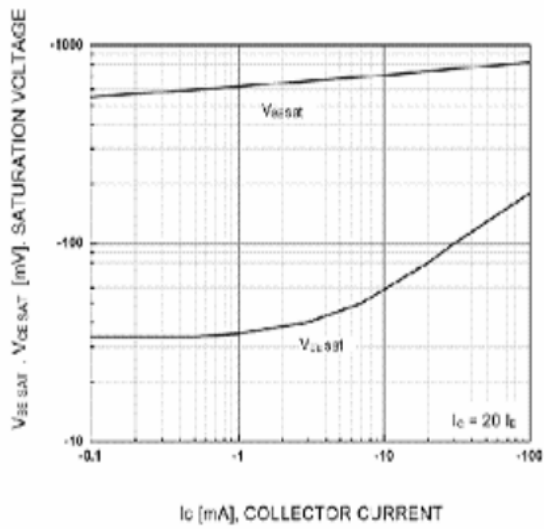
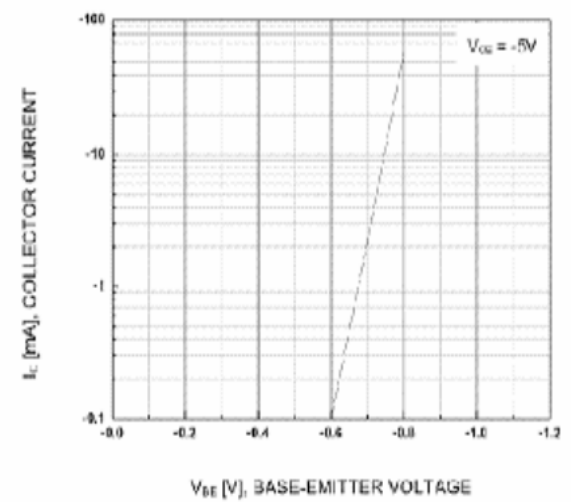
| Symbol<br>(符号) | Parameter<br>(参数名称)                   | Value<br>(额定值) | Units<br>(单位) |
|----------------|---------------------------------------|----------------|---------------|
| <b>VCBO</b>    | Collector-Base Voltage (集电极-基极电压)     | -50            | V             |
| <b>VCEO</b>    | Collector-Emitter Voltage (集电极-发射极电压) | -45            | V             |
| <b>VEBO</b>    | Emitter-Base Voltage (发射极-基极电压)       | -5             | V             |
| <b>IC</b>      | Collector Current -Continuous (集电极电流) | -0.1           | A             |
| <b>PC</b>      | Collector Power Dissipation (耗散功率)    | 0.2            | W             |
| <b>Tj</b>      | Junction Temperature (结温)             | 150            | °C            |
| <b>Tstg</b>    | Storage Temperature (储存温度)            | -55-150        | °C            |

**ELECTRICAL CHARACTERISTICS** (Tamb=25°C unless otherwise specified)

| Parameter<br>(参数名称)                                 | Symbol<br>(符号) | Test conditions<br>(测试条件) | MIN<br>(最小值) | TYP<br>(典型值) | MAX<br>(最大值) | UNIT<br>(单位) |
|---|----------------|---------------------------|--------------|--------------|--------------|--------------|
| Collector-base breakdown voltage<br>集电极-基极击穿电压      | V(BR)CBO       | IC= -100μA, IE=0          | -50          |              |              | V            |
| Collector-emitter breakdown voltage<br>集电极-发射极击穿电压  | V(BR)CEO       | IC= -1mA, IB=0            | -45          |              |              | V            |
| Emitter-base breakdown voltage<br>发射极-基极击穿电压        | V(BR)EBO       | IE=-100μA, IC=0           | -5           |              |              | V            |
| Collector cut-off current<br>集电极-基极截止电流             | ICBO           | VCB=-50 V, IE=0           |              |              | -1           | μ A          |
| Collector cut-off current<br>集电极-发射极截止电流            | ICEO           | VCE=-35V, IB=0            |              |              | -10          | μ A          |
| Emitter cut-off current<br>发射极-基极截止电流               | IEBO           | VEB=-5V, IC=0             |              |              | -1           | μ A          |
| DC current gain<br>直流电流增益                           | hFE            | VCE=-5V, IC= -1mA         | 80           |              | 600          |              |
| Collector-emitter saturation voltage<br>集电极-发射极饱和压降 | VCE(sat)       | IC=-100mA, IB= -5mA       |              |              | -0.3         | V            |
| Base-emitter saturation voltage<br>发射极-基极饱和压降       | VBE(sat)       | IC=-100mA, IB= -5mA       |              |              | -1           | V            |

**CLASSIFICATION OF hFE**

| Range | 80-200 | 200-400 | 400-600 |
|-------|--------|---------|---------|
|       |        |         |         |

**Typical Characteristics**

**Figure 1. Static Characteristic**

**Figure 2. DC current Gain**

**Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage**

**Figure 4. Base-Emitter On Voltage**